

**IN THE CLAIMS:**

Please substitute the following claims for the same-numbered claims in the application:

1. (Currently Amended) A semiconductor structure having at least one fin-type field effect transistor (FinFET), said semiconductor structure comprising:

a substrate;

fins, comprising at least one first fin and at least one second fin, extending from said substrate; and

a first gate dielectrics covering opposing sides of said first fins, and a second gate dielectric covering opposing sides of said second fin,

wherein said first gate dielectric has a first thickness and said second gate dielectric has a second thickness and wherein said gate dielectrics have different thicknesses than said second gate dielectric first thickness is different from said second thickness.

2. (Currently Amended) The semiconductor structure in claim 1, wherein said first fin and said second fin are utilized in different types of transistors on said substrate; and wherein one type of transistor includes gate dielectrics having a first thickness and a second type of transistor includes gate dielectrics having a second thickness different than said first thickness, wherein said different transistors have different voltage requirements.

3. (Currently Amended) A semiconductor structure having at least one fin-type field effect transistor (FinFET), said semiconductor structure comprising The semiconductor structure in claim 1,:

a substrate;

fins extending from said substrate; and

gate dielectrics covering said fins,

wherein said gate dielectrics have different thicknesses and wherein said fins are utilized in at least one multiple-fin transistor.

4. (Previously Presented) The semiconductor structure in claim 1, wherein thicker gate dielectrics comprise multiple layers of dielectric and thinner gate dielectrics comprise less layers of dielectric.

5. (Previously Presented) The semiconductor structure in claim 1, further comprising a cap over said fins.

6. (Currently Amended) The semiconductor structure in claim 5, wherein said cap comprises a different material than said first gate dielectrics and said second gate dielectric.

7. (Currently Amended) A semiconductor structure having at least one fin-type field effect transistor (FinFET), said semiconductor structure comprising:

a substrate;

fins, comprising at least one first fin and at least one second fin, extending from said substrate, wherein each of said fins comprises a central channel region and source and drain regions on opposite sides ends of said channel region; and

a first gate dielectric covering opposing sides of said channel region of said first fin and a second gate dielectric covering opposing sides of said channel region of said second fin,

gate dielectrics covering said channel regions of each of said fins,  
wherein said first gate dielectric has a first thickness and said second gate dielectric has a second thickness, wherein said first thickness is different from said second thickness and wherein said gate dielectrics and said fins have different thicknesses.

8. (Currently Amended) The structure in claim 7, wherein said fins first fin and said second fin are utilized in different types of transistors on said substrate, and wherein one type of transistor includes gate dielectrics having a first thickness and a second type of transistor includes gate dielectrics having a second thickness different than said first thickness, wherein said different transistors have different voltage requirements.

9. (Currently Amended) A semiconductor structure having at least one fin-type field effect transistor (FinFET), said semiconductor structure comprising The semiconductor structure in claim 7,:

a substrate;

fins extending from said substrate, wherein each of said fins comprises a central channel region and source and drain regions on opposite sides of said channel region; and gate dielectrics covering said channel regions of each of said fins,

wherein said gate dielectrics and said fins have different thicknesses and wherein said fins are utilized in at least one multiple-fin transistor.

10. (Previously Presented) The semiconductor structure in claim 7, wherein thicker gate dielectrics comprise multiple layers of dielectric and thinner gate dielectrics comprise less layers of dielectric.

11. (Previously Presented) The semiconductor structure in claim 7, further comprising a cap over said fins.

12. (Currently Amended) The semiconductor structure in claim 11, wherein said cap comprises a different material than said first gate dielectrics and said second gate dielectric.

13. (Currently Amended) A semiconductor structure having multiple fin-type field effect transistors (FinFETs), said semiconductor structure comprising:

a substrate;

complementary transistors on said substrate, wherein said complementary transistors comprise:

fins a first fin for a first type transistor and a second fin for a second type transistor extending from said substrate; and

a first gate dielectrics covering opposing sides of said first fins and a second gate dielectric covering opposing sides of said second fin,

wherein said first gate dielectric has a first thickness and said second gate dielectric has a second thickness and wherein said first thickness is different from said second thickness wherein said fins are utilized in different types of transistors on said substrate, and wherein a first type of transistor includes gate dielectrics having a first thickness and a second type of transistor includes gate dielectrics having a second thickness different than said first thickness.

14. (Currently Amended) A semiconductor structure having multiple fin-type field effect transistors (FinFETs), said semiconductor structure comprising The semiconductor structure in claim 13,;

a substrate;

fins extending from said substrate; and

gate dielectrics covering said fins,

wherein said fins are utilized in different types of transistors on said substrate, and wherein a first type of transistor includes gate dielectrics having a first thickness and a second type of transistor includes gate dielectrics having a second thickness different than said first thickness and wherein said fins are utilized in multiple-fin transistors.

15. (Previously Presented) The semiconductor structure in claim 13, wherein thicker gate dielectrics comprise multiple layers of dielectric and thinner gate dielectrics comprise less layers of dielectric.

16. (Previously Presented) The semiconductor structure in claim 13, further comprising a cap over said fins.

17. (Currently Amended) The semiconductor structure in claim 13, wherein said cap comprises a different material than said first gate dielectrics and said second gate dielectric.

18-34. (Canceled).